

2SA1478/2SC3788

High-Definition CRT Display Video Output Applications

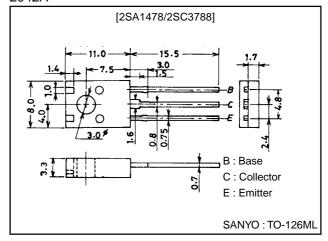
Features

- · High breakdown voltage : $V_{CEO} \ge 200V$.
- · Small reverse transfer capacitance and excellent high frequency cahaceteristic
 - : C_{re}=1.2pF (NPN), 1.7pF (PNP).
- · Adoption of FBET process.

Package Dimensions

unit:mm

2042A



(): 2SA1478

Specifications

Absolute Maximum Ratings at Ta = 25°C

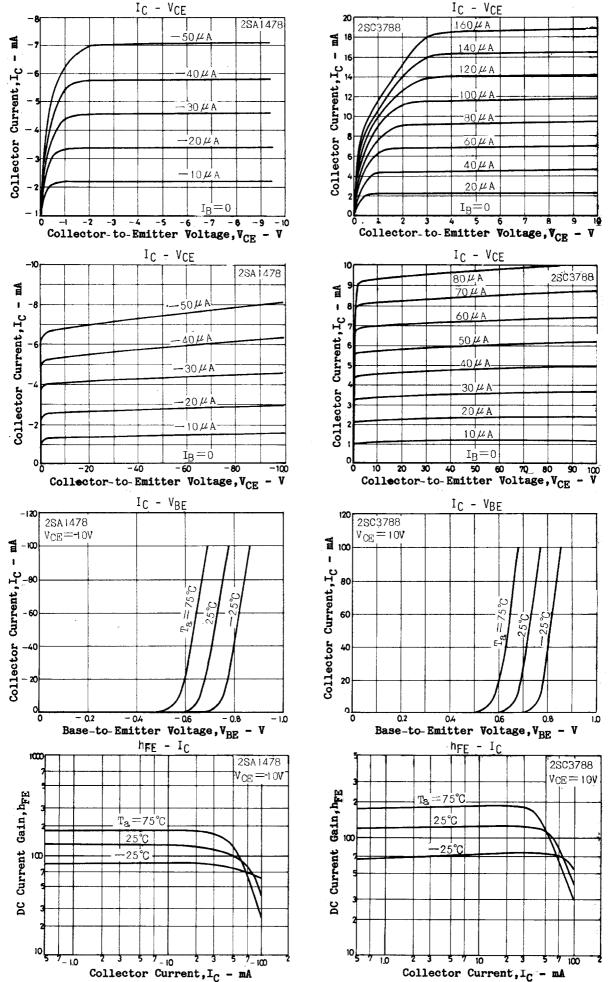
Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		(-)200	V
Collector-to-Emitter Voltage	VCEO		(-)200	V
Emitter-to-Base Voltage	VEBO		(-)5	V
Collector Current	IC		(–)100	mA
Peak Collector Current	I _{CP}		(–)200	mA
Collector Dissipation	PC		1.3	W
		Tc=25°C	5	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

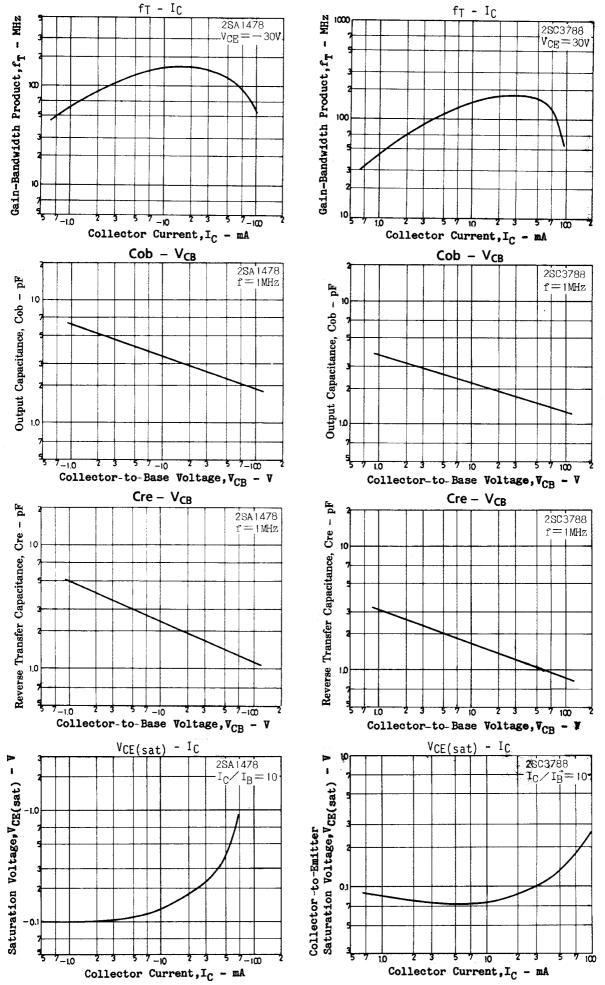
Electrical Characteristics at Ta = 25°C

Parameter	Cumph of	Condition -	Ratings			1.114
	Symbol	Conditions		typ	max	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} =(-)150V, I _E =0			(–)0.1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =(-)4V, I _C =0			(-)0.1	μA
DC Current Gain	hFE	V _{CE} =(-)10V, I _C =(-)10mA	40*		320*	
Gain-Bandwidth Product	fT	V _{CE} =(-)30V, I _C =(-)10mA		150		MHz
Output Capacitance	C _{ob}	V _{CB} =(-)30V, f=1MHz		1.7		pF
				(2.6)		pF
Reverse Transfer Capacitance	C _{re}	VCB=(-)30V, f=1MHz		1.2		pF
				(1.7)		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =(-)20mA, I _B =(-)2mA			(-)0.6	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =(-)20mA, I _B =(-)2mA			(-)1.0	V
Collector-to-Base Breakdown Voltage	V _(BR) CBO	I _C =(-)10μΑ, I _E =0	(-)200			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =(−)1mA, R _{BE} =∞	(-)200			V
Emitter-to-Base Breakdown Votage	V(BR)EBO	I _E =(-)10μΑ, I _C =0	(-)5			V

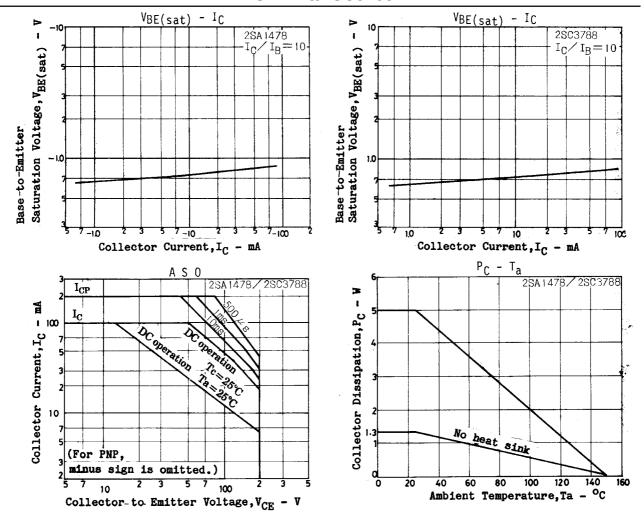
 $[\]ensuremath{^*}$: The 2SA1478/2SC3788 are classified by 10mA $\ensuremath{h_{FE}}$ as follows:

40 C 80	60 D 120	100 E 200	160 F 320
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2SA1478/2SC3788



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